Features

- Single 3.3V ±10% Supply
- Fast Read Access Time – 200 ns
- Automatic Page Write Operation
  - Internal Address and Data Latches for 128 Bytes
  - Internal Control Timer
- Fast Write Cycle Time
  - Page Write Cycle Time – 10 ms Maximum
  - 1 to 128-Byte Page Write Operation
- Low Power Dissipation
  - 15 mA Active Current
  - 20 µA CMOS Standby Current
- Hardware and Software Data Protection
- $\overline{\text{DATA}}$ Polling for End of Write Detection
- High Reliability CMOS Technology
  - Endurance: 10^5 Cycles
  - Data Retention: 10 Years
- JEDEC Approved Byte-Wide Pinout
- Industrial and Automotive Temperature Ranges
- Green (Pb/Halide-free) Packaging Option

1-Megabit (128K x 8) Low Voltage Paged Parallel EEPROMs

AT28LV010

1. Description

The AT28LV010 is a high-performance 3-volt only Electrically Erasable and Programmable Read-Only Memory. Its 1 megabit of memory is organized as 131,072 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 200 ns with power dissipation of just 54 mW. When the device is deselected, the CMOS standby current is less than 20 µA.

The AT28LV010 is accessed like a Static RAM for the read or write cycle without the need for external components. The device contains a 128-byte page register to allow writing of up to 128 bytes simultaneously. During a write cycle, the address and 1 to 128 bytes of data are internally latched, freeing the address and data bus for other operations. Following the initiation of a write cycle, the device will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by $\overline{\text{DATA}}$ polling of I/O7. Once the end of a write cycle has been detected a new access for a read or write can begin.

Atmel's 28LV010 has additional features to ensure high quality and manufacturability. The device utilizes internal error correction for extended endurance and improved data retention characteristics. Software data protection is implemented to guard against inadvertent writes. The device also includes an extra 128 bytes of EEPROM for device identification or tracking.

5. DC and AC Operating Range

		AT28LV010-20	AT28LV010-25
Operating Temperature (Case)	Ind.	-40°C - 85°C	-40°C - 85°C
	Automotive	-40°C - 125°C	
V_{CC} Power Supply		3.3V ±5%	3.3V ±10%

6. Operating Modes

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O
Read	V_{IL}	V_{IL}	V_{IH}	D_{OUT}
Write[2]	V_{IL}	V_{IH}	V_{IL}	D_{IN}
Standby/Write Inhibit	V_{IH}	X[1]	X	High Z
Write Inhibit	X	X	V_{IH}	
Write Inhibit	X	V_{IL}	X	
Output Disable	X	V_{IH}	X	High Z

Notes: 1. X can be V_{IL} or V_{IH}.
2. Refer to AC Programming Waveforms.

7. Absolute Maximum Ratings*

Temperature Under Bias ..... -55°C to +125°C

Storage Temperature ..... -65°C to +150°C

All Input Voltages (including NC Pins) with Respect to Ground .....-0.6V to +6.25V

All Output Voltages with Respect to Ground .....-0.6V to V_{CC} + 0.6V

Voltage on $\overline{OE}$ and A9 with Respect to Ground .....-0.6V to +13.5V

*NOTICE: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

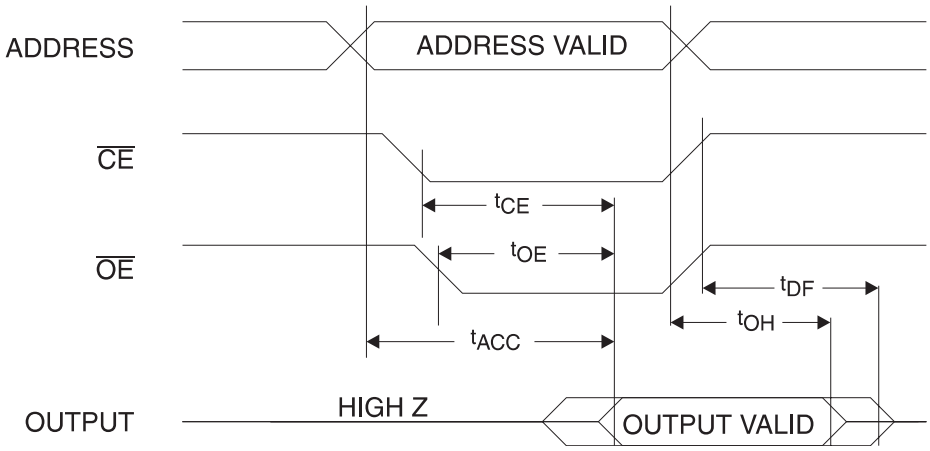
8. DC Characteristics

Symbol	Parameter	Condition		Min	Max	Units
I_{LI}	Input Load Current	V_{IN} = 0V to V_{CC}			1	µA
I_{LO}	Output Leakage Current	$V_{I/O}$ = 0V to V_{CC}			1	µA
I_{SB}	V_{CC} Standby Current CMOS	$\overline{CE}$ = V_{CC} - 0.3V to V_{CC} + 1V	Ind.		50	µA
I_{CC}	V_{CC} Active Current	f = 5 MHz; I_{OUT} = 0 mA; V_{CC} = 3.6V			15	mA
V_{IL}	Input Low Voltage				0.8	V
V_{IH}	Input High Voltage			2.0		V
V_{OL}	Output Low Voltage	I_{OL} = 1.6 mA; V_{CC} = 3.0V			0.45	V
V_{OH}	Output High Voltage	I_{OH} = -100 µA; V_{CC} = 3.0V		2.4		V

9. AC Read Characteristics

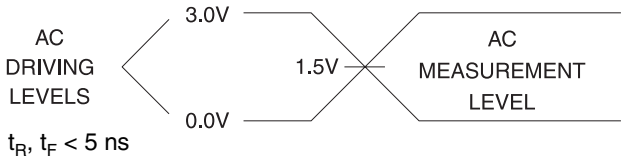
Symbol	Parameter	AT28LV010-20		Units
		Min	Max	
t_{ACC}	Address to Output Delay		200	ns
t_{CE}[1]	$\overline{CE}$ to Output Delay		200	ns
t_{OE}[2]	$\overline{OE}$ to Output Delay	0	80	ns
t_{DF}[3][4]	$\overline{CE}$ or $\overline{OE}$ to Output Float	0	55	ns
t_{OH}	Output Hold from $\overline{OE}$, $\overline{CE}$ or Address, Whichever Occurred First	0		ns

10. AC Read Waveforms[1][2][3][4]

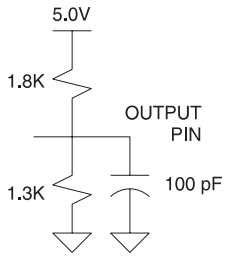


Notes:
1. $\overline{CE}$ may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on t_{ACC}.
2. $\overline{OE}$ may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of $\overline{CE}$ without impact on t_{CE} or by $t_{ACC} - t_{OE}$ after an address change without impact on t_{ACC}.
3. t_{DF} is specified from $\overline{OE}$ or $\overline{CE}$ whichever occurs first (C_L = 5 pF).
4. This parameter is characterized and is not 100% tested.

11. Input Test Waveforms and Measurement Level



12. Output Test Load



13. Pin Capacitance

f = 1 MHz, T = 25°C[1]

Symbol	Typ	Max	Units	Conditions
C_{IN}	4	6	pF	V_{IN} = 0V
C_{OUT}	8	12	pF	V_{OUT} = 0V

Note: 1. This parameter is characterized and is not 100% tested.

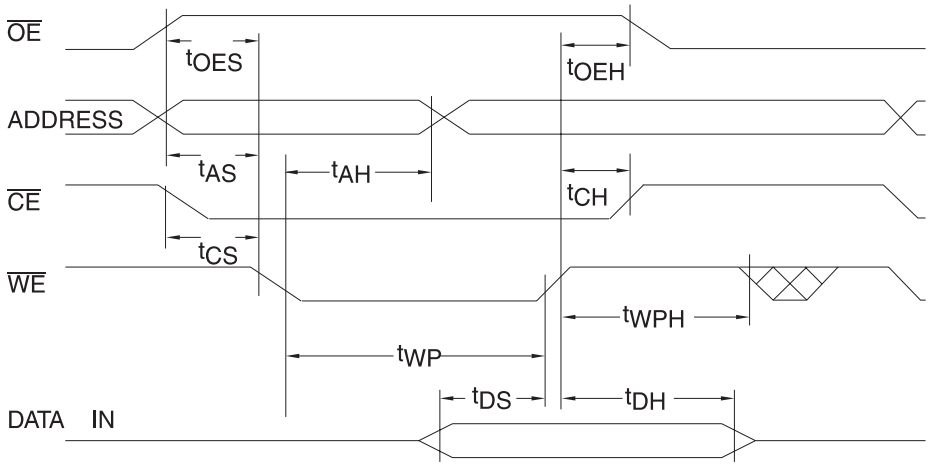
14. AC Write Characteristics[1]

Symbol	Parameter	Min	Max	Units
t_{AS}, t_{OES}	Address, $\overline{OE}$ Set-up Time	0		ns
t_{AH}	Address Hold Time	100		ns
t_{CS}	Chip Select Set-up Time	0		ns
t_{CH}	Chip Select Hold Time	0		ns
t_{WP}	Write Pulse Width ($\overline{WE}$ or $\overline{CE}$)	200		ns
t_{DS}	Data Set-up Time	100		ns
t_{DH}, t_{OEH}	Data, $\overline{OE}$ Hold Time	10		ns

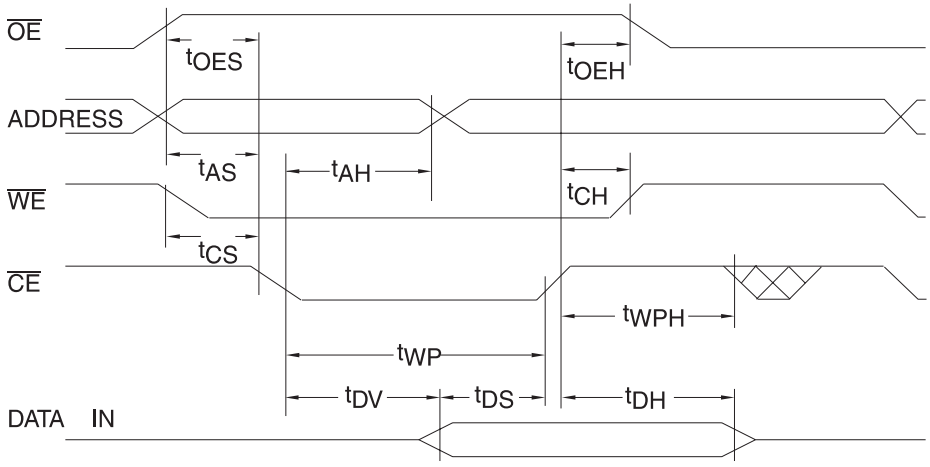
Note: 1. All write operations must be preceded by the SDP command sequence.

15. AC Write Waveforms

15.1 $\overline{WE}$ Controlled



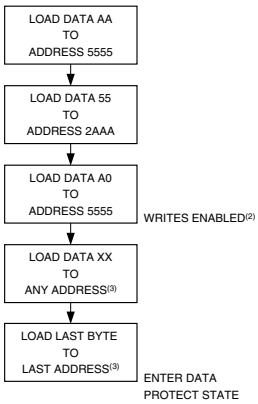
15.2 $\overline{CE}$ Controlled



16. Software Protected Write Characteristics

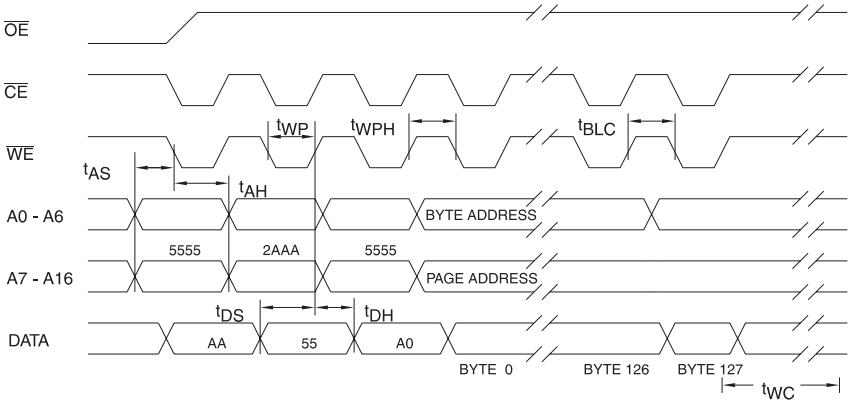
Symbol	Parameter	Min	Max	Units
t_{WC}	Write Cycle Time		10	ms
t_{AS}	Address Set-up Time	0		ns
t_{AH}	Address Hold Time	100		ns
t_{DS}	Data Set-up Time	100		ns
t_{DH}	Data Hold Time	10		ns
t_{WP}	Write Pulse Width	200		ns
t_{BLC}	Byte Load Cycle Time		150	µs
t_{WPH}	Write Pulse Width High	100		ns

17. Programming Algorithm



Notes:
1. Data Format: I/O7 - I/O0 (Hex); Address Format: A14 - A0 (Hex).
2. Data protect state will be re-activated at the end of program cycle.
3. 1 to 128 bytes of data are loaded.

18. Software Protected Program Cycle Waveforms(1)(2)(3)



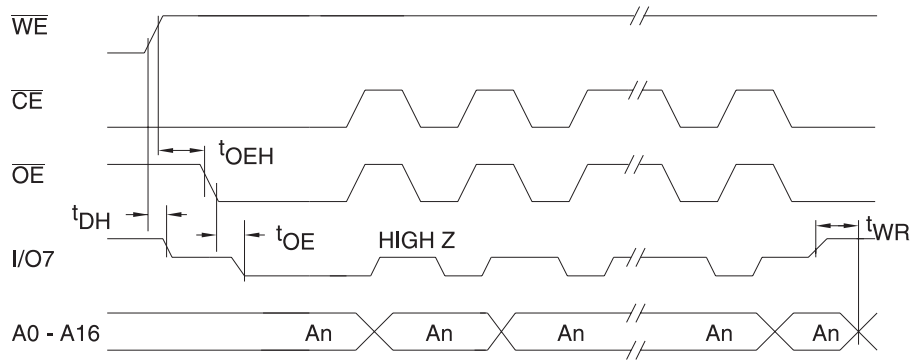
Notes:
1. A0 - A14 must conform to the addressing sequence for the first three bytes as shown above.
2. After the command sequence has been issued and a page write operation follows, the page address inputs (A7 - A16) must be the same for each high to low transition of $\overline{WE}$ (or $\overline{CE}$).
3. $\overline{OE}$ must be high only when $\overline{WE}$ and $\overline{CE}$ are both low.

19. $\overline{\text{Data}}$ Polling Characteristics[1]

Symbol	Parameter	Min	Typ	Max	Units
t_{DH}	Data Hold Time	10			ns
t_{OEH}	$\overline{OE}$ Hold Time	10			ns
t_{OE}	$\overline{OE}$ to Output Delay[2]				ns
t_{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.
2. See AC Read Characteristics

20. $\overline{\text{Data}}$ Polling Waveforms

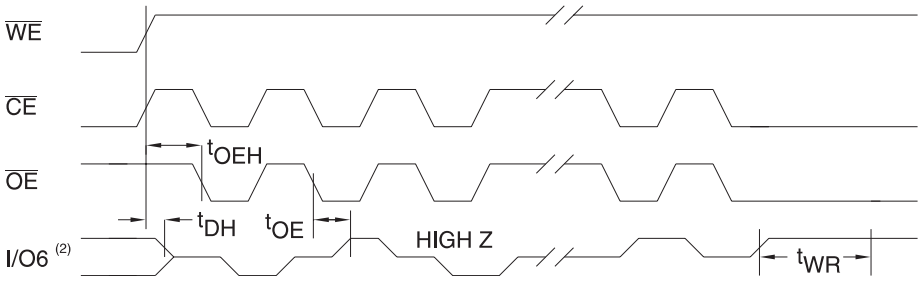


21. Toggle Bit Characteristics[1]

Symbol	Parameter	Min	Typ	Max	Units
t_{DH}	Data Hold Time	10			ns
t_{OEH}	$\overline{OE}$ Hold Time	10			ns
t_{OE}	$\overline{OE}$ to Output Delay[2]				ns
t_{OEHP}	$\overline{OE}$ High Pulse	150			ns
t_{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.
2. See AC Read Characteristics

22. Toggle Bit Waveforms



Notes: 1. Toggling either $\overline{OE}$ or $\overline{CE}$ or both $\overline{OE}$ and $\overline{CE}$ will operate toggle bit.
2. Beginning and ending state of I/O6 will vary.
3. Any address location may be used but the address should not vary.

23. Ordering Information[1]

23.1 Standard Package

t_{ACC} (ns)	I_{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
200	15	0.05	AT28LV010-20JI AT28LV010-20PI AT28LV010-20TI	32J 32P6 32T	Industrial (-40° to 85° C)
250	15	0.05	AT28LV010-25JI AT28LV010-25PI AT28LV010-25TI	32J 32P6 32T	Industrial (-40° to 85° C)

Note: 1. See “Valid Part Numbers” below.

23.2 Green Package Option (Pb/Halide-free)

t_{ACC} (ns)	I_{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
200	15	0.05	AT28LV010-20JU AT28LV010-20PU AT28LV010-20TU	32J 32P6 32T	Industrial (-40° to 85° C)

Package Type	
32J	32-Lead, Plastic J-Leaded Chip Carrier (PLCC)
32P6	32-Lead, 0.600” Wide, Plastic Dual Inline Package (PDIP)
32T	32-Lead, Plastic Thin Small Outline Package (TSOP)

24. Valid Part Numbers

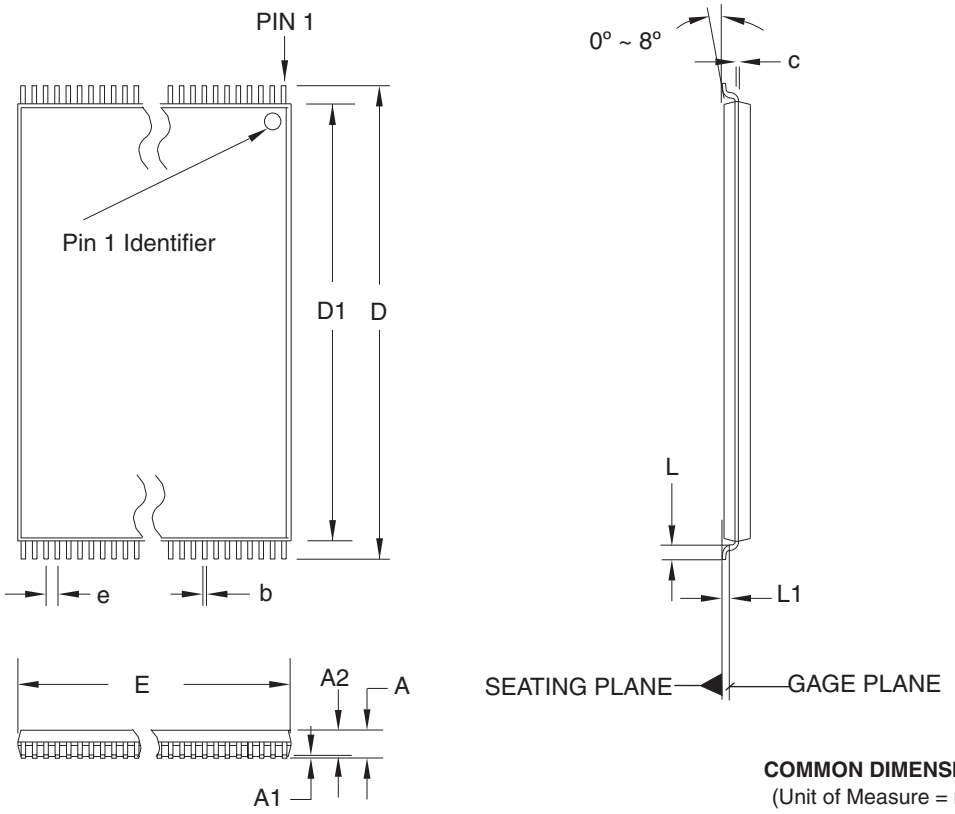
The following table lists standard Atmel products that can be ordered.

Device Numbers	Speed	Package and Temperature Combinations
AT28LV010	20	JI, JU, PI, TI, TU, PU

25. Die Products

Reference Section: Parallel EEPROM Die Products

26.3 32T – TSOP



COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	–	–	1.20	
A1	0.05	–	0.15	
A2	0.95	1.00	1.05	
D	19.80	20.00	20.20	
D1	18.30	18.40	18.50	Note 2
E	7.90	8.00	8.10	Note 2
L	0.50	0.60	0.70	
L1	0.25 BASIC			
b	0.17	0.22	0.27	
c	0.10	–	0.21	
e	0.50 BASIC			

Notes:
1. This package conforms to JEDEC reference MO-142, Variation BD.
2. Dimensions D1 and E do not include mold protrusion. Allowable protrusion on E is 0.15 mm per side and on D1 is 0.25 mm per side.
3. Lead coplanarity is 0.10 mm maximum.

	TITLE	DRAWING NO.	REV.
2325 Orchard Parkway San Jose, CA 95131	**32T**, 32-lead (8 x 20 mm Package) Plastic Thin Small Outline Package, Type I (TSOP)	32T	B